# Diodes, Dual 40 Watt Peak Power, High Temperature

SC-70 Dual Common Anode Zeners

# MMBZHxxVAWT1G Series, SZMMBZHxxVAWT1G Series

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage ESD protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are high temperature rated and ideal for use in high reliability applications where board space is at a premium.

#### **Features**

- SC-70 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range: 12 33 V
- Peak Power 40 W @ 1.0 ms (Unidirectional), per Figure 5 Waveform
- ESD Rating:
  - Class 3B (> 16 kV) per the Human Body Model
  - Class C (> 400 V) per the Machine Model
- Low Leakage < 5.0 μA
- Flammability Rating UL 94 V-0
- 175°C T<sub>J(MAX)</sub> Rated for High Temperature, Mission Critical Applications
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices\*

#### **Mechanical Characteristics:**

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

## **MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

1

260°C for 10 Seconds

Package designed for optimal automated board assembly Small package size for high density applications Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel.

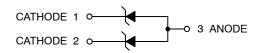


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SC-70 CASE 419 STYLE 4



#### **MARKING DIAGRAM**



XX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBZHxxVAWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SZMMBZHxxVAWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **DEVICE MARKING INFORMATION**

See specific marking information in the device marking column of the table on page 2 of this data sheet.

# MMBZHxxVAWT1G Series, SZMMBZHxxVAWT1G Series

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ T <sub>L</sub> ≤ 25°C	P <sub>pk</sub>	40	W
Total Power Dissipation on FR–5 Board (Note 2)  @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.5	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	605	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

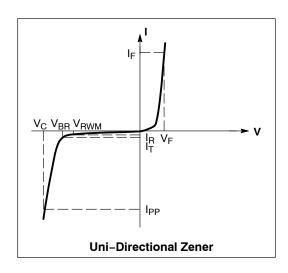
- 1. Non-repetitive current pulse per Figure 5 and derate above  $T_A = 25^{\circ}C$  per Figure 6.
- 2.  $FR-5 = 1.0 \times 0.75 \times 0.62$  in.

### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
ΘV <sub>BR</sub>	Maximum Temperature Coefficient of V <sub>BR</sub>
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
Z <sub>ZT</sub>	Maximum Zener Impedance @ I <sub>ZT</sub>
I <sub>ZK</sub>	Reverse Current
Z <sub>ZK</sub>	Maximum Zener Impedance @ I <sub>ZK</sub>



# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) **UNIDIRECTIONAL** (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max} @ I_F = 10 \text{ mA})$ 

			I <sub>R</sub> @	Breakdown Voltage			V <sub>C</sub> @ I <sub>PP</sub>	(Note 4)		
	Device	V <sub>RWM</sub>	V <sub>RWM</sub>	V <sub>B</sub>	R (Note 3)	(V)	@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	$\Theta V_{BR}$
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZH12VAWT1G	CK	8.5	200	11.40	12	12.60	1.0	17	2.35	7.5
MMBZH15VAWT1G	AJ	12	50	14.25	15	15.75	1.0	21	1.9	12.3
MMBZH20VAWT1G**	-	17	50	19.00	20	21.00	1.0	28	1.4	17.2
MMBZH27VAWT1G**	-	22	50	25.65	27	28.35	1.0	40	1.0	24.3
MMBZH33VAWT1G**	-	26	50	31.35	33	34.65	1.0	46	0.87	30.4

<sup>3.</sup>  $V_{BR}$  measured at pulse test current  $I_T$  at an ambient temperature of 25°C.

<sup>4.</sup> Surge current waveform per Figure 5 and derate per Figure 6.

<sup>\*</sup>Includes SZ prefix devices where applicable.

<sup>\*\*</sup>AEC-Q release available upon request.

# MMBZHxxVAWT1G Series, SZMMBZHxxVAWT1G Series

#### **TYPICAL CHARACTERISTICS**

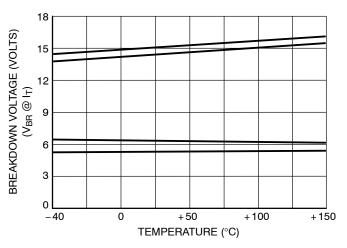


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve for each voltage is bidirectional mode, lower curve is unidirectional mode)

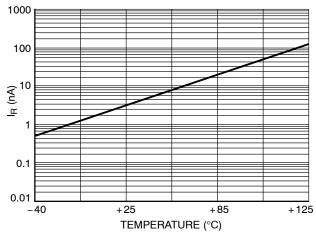


Figure 2. Typical Leakage Current versus Temperature

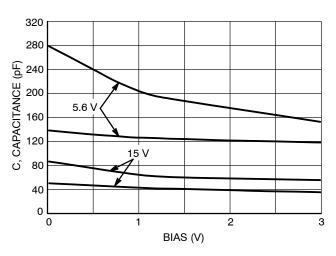


Figure 3. Typical Capacitance versus Bias Voltage (Upper curve for each voltage is unidirectional mode, lower curve is bidirectional mode)

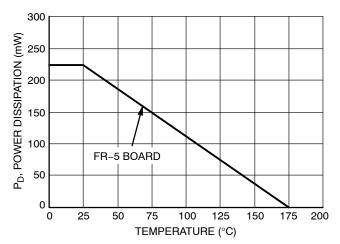


Figure 4. Steady State Power Derating Curve

## MMBZHxxVAWT1G Series, SZMMBZHxxVAWT1G Series

#### **TYPICAL CHARACTERISTICS**

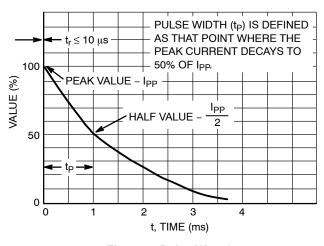


Figure 5. Pulse Waveform

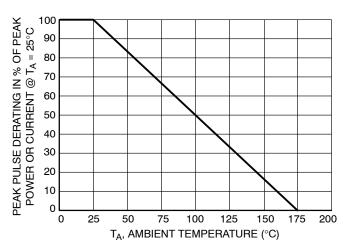


Figure 6. Pulse Derating Curve

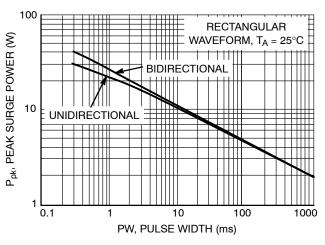


Figure 7. Maximum Non-repetitive Surge Power,  $P_{pk}$  versus PW

Power is defined as  $V_{RSM} \ x \ I_Z(pk)$  where  $V_{RSM}$  is the clamping voltage at  $I_Z(pk).$ 

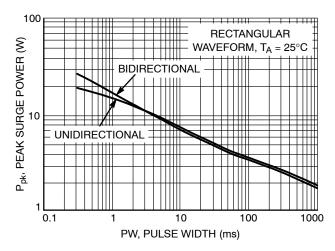


Figure 8. Maximum Non-repetitive Surge Power, Ppk (NOM) versus PW

Power is defined as  $V_Z(NOM) \times I_Z(pk)$  where  $V_Z(NOM)$  is the nominal Zener voltage measured at the low test current used for voltage classification.





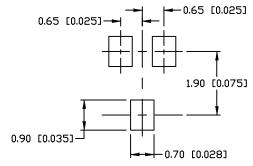
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**DATE 07 OCT 2021** 

#### NOTES:

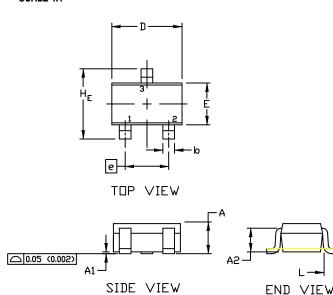
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M]	LLIMETE	RS	INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
Ε	1.15	1.24	1.35	0.045	0.049	0.053	
e	1.20	1.30	1.40	0.047	0.051	0.055	
e1		0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	
				`			



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



# GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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